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APPLICATION NO	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO	CONFIRMATION NO
09 753,664	01 04 2001	Liming Tsau	1875.0230000	1902
26111 -	590 03 27 2002			
STERNE, KESSLER, GOLDSTEIN & FOX PLLC			EXAMINER	
	1100 NEW YORK AVENUE, N.W., SUITE 600 WASHINGTON, DC 20005-3934		BRAIRTON, SCOTT A	
			ART UNIT	PAPER NUMBER
			2823	

DATE MAILED: 03 27 2002

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	pplicant(s)				
•	09/753,664	TSAU, LIMING				
Office Action Summary	Examiner	Art Unit				
	Scott A Brairton	2823				
The MAILING DATE of this communication app Period for Reply	ears on the cover s	heet with the correspondence address				
A SHORTENED STATUTORY PERIOD FOR REPLY THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a reply - If NO period for reply is specified above, the maximum statutory period w - Failure to reply within the set or extended period for reply will, by statute, - Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b). Status	36(a). In no event, however within the statutory minimularity and will expire Statution to be	er, may a reply be timely filed num of thirty (30) days will be considered timely. X (6) MONTHS from the mailing date of this communication. Decome ABANDONED (35 U.S.C. § 133).				
1) Responsive to communication(s) filed on 21 S	September 2001 .					
2a) ☐ This action is FINAL . 2b) ☑ Th	is action is non-fin	al.				
3) Since this application is in condition for allowated closed in accordance with the practice under a Disposition of Claims						
4) Claim(s) 1-18 is/are pending in the application	l.					
4a) Of the above claim(s) is/are withdraw	wn from considerat	ion.				
5) Claim(s) is/are allowed.						
6) Claim(s) 1-18 is/are rejected.						
7) Claim(s) is/are objected to.						
8) Claim(s) are subject to restriction and/o	r election requirem	ient.				
Application Papers						
9) The specification is objected to by the Examine	r.					
10)☑ The drawing(s) filed on 21 September 2001 is/a	ire: a)⊠ accepted o	or b) objected to by the Examiner .				
Applicant may not request that any objection to the						
11) The proposed drawing correction filed on						
If approved, corrected drawings are required in rep		on.				
12) The oath or declaration is objected to by the Ex	aminer.					
Priority under 35 U.S.C. §§ 119 and 120						
13) Acknowledgment is made of a claim for foreign	n priority under 35	U.S.C. § 119(a)-(d) or (f).				
a) All b) Some * c) None of:						
1. Certified copies of the priority document						
2. Certified copies of the priority document	s have been receiv	ved in Application No				
 3. Copies of the certified copies of the prior application from the International Bu * See the attached detailed Office action for a list 	reau (PCT Rule 17	7.2(a)).				
14) Acknowledgment is made of a claim for domesti	c priority under 35	U.S.C. § 119(e) (to a provisional application).				
a) The translation of the foreign language pro	, ,					
Attachment(s)						
 Notice of References Cited (PTO-892) Notice of Draftsperson's Patent Drawing Review (PTO-948) Information Disclosure Statement(s) (PTO-1449) Paper No(s)	5)	Interview Summary (PTO-413) Paper No(s) Notice of Informal Patent Application (PTO-152) Other:				
S Patent and Trademark Office	ntion Cummary	Part of Paper No. 6				

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DETAILED ACTION

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 1-18 are rejected under 35 U.S.C. 103(a) as being unpatentable over Jang et al (U.S. Patent No. 6,297,162) in combination with Parikh (U.S. Patent No. 6,225,207).

Jang et al disclose in figures 1-15 and related text a method of forming a semiconductor device comprising the steps of forming a first dielectric layer (figure 4, 43) comprising silicon oxide (col. 1, lines 35-40) on a substrate (figure 4, 41), forming a metal layer comprising copper (figure 4, 42, and col. 2, lines 5-10) in the first dielectric layer wherein the metal layer does not extend all the way down to the substrate (figure 4), forming a stop layer (figure 4, 44) comprising silicon nitride (col. 2, lines 15-20) on the first dielectric layer and the first metal layer, forming a second dielectric layer (figure 4, 45) on the stop layer, wherein the first and second dielectric layers are thicker than the stop layer (figure 4).

Jang et al fails to expressly disclose using masks to pattern the dielectric layers as well as forming two openings in the second dielectric layer that expose portions of the stop layer and then using a third mask to remove a second portion of the second dielectric layer and a portion of the stop layer, thereby exposing a portion of the metal layer, and finally filling the openings in the second dielectric layer with a copper or copper alloy.

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Parikh discloses in figures 1-13 and related text a method of forming a patterned masking layer (figure 3A, 322) over the substrate (figure 3A, 310 such that a portion of the second dielectric layer (figure 3A, 320) is exposed; removing the exposed portion of the second dielectric layer (figure 3B) so that a first opening (figure 3B, 326) and a second opening (figure 3B, 324) are formed in the second dielectric layer, thereby exposing portions of the stop layer (figure 3B, 314); forming a third patterned masking layer (figure 3D, 325) over the substrate such that a further portion of the second dielectric layer and a portion of the stop layer are exposed; removing the exposed portions of the second dielectric layer and the stop layer (figure 3E); and filling the first and second openings with a copper or copper alloy thereby forming a second metal layer (figure 3F, 350, col. 7, lines 64+). Parikh further discloses chemical mechanical polishing second metal layer 350 (col. 8, lines 1+).

It would have been obvious to one of ordinary skill in the art at the time of the invention to combine the method of Parikh with the method of Jang et al in order to provide for a cost effective, improved technique for damascene fabrication (col. 2, lines 50-55).

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Scott A Brairton whose telephone number is (703) 605-4213. The examiner can normally be reached on M-F, 8:30AM-5:00PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Wael Fahmy can be reached on (703) 308-4918. The fax phone numbers for the

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organization where this application or proceeding is assigned are (703) 746-4082 for regular communications and (703) 746-4082 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

Scott A Brairton Examiner Art Unit 2823

sab March 19, 2002

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